

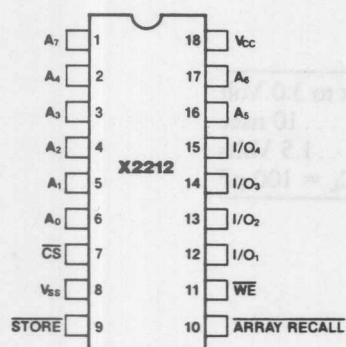
## 256 x 4 Bit Nonvolatile Static RAM 5V-Programmable

X2212-30

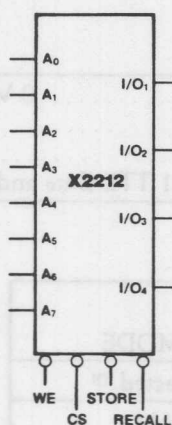
- **NONVOLATILE STATIC RAM:** The X2212 contains 2K bits of memory organized as a conventional 1K static RAM overlaid bit-for-bit with a nonvolatile 1K Electrically Erasable PROM (E<sup>2</sup>PROM). Nonvolatile data can be stored in the E<sup>2</sup>PROM and at the same time independent data can be accessed in the RAM memory. At any time, data can be transferred back-and-forth between the RAM and E<sup>2</sup>PROM by simple store and array recall signals.
- **5V-PROGRAMMABLE:** High-voltage pulses or supplies are never required. A single 5V supply is the only power source ever required for any function.
- **EASE-OF-USE:** Unprecedented simplicity, all inputs and outputs are directly TTL compatible. Fully static timing. 18-pin package.
- **PERFORMANCE:** RAM cycle time is less than 300 ns. During the lifetime of the device, data can be recalled from the E<sup>2</sup>PROM an unlimited number of times.
- **POWER-FAILURE PROTECTION:** One simple TTL signal saves the entire RAM database. A snapshot nonvolatile copy of all RAM data is internally stored safe without power and can be recalled to the RAM when power returns. No battery backup required.
- **ORGANIZED FOR MICROCOMPUTER SYSTEMS:** The common data input and output is organized four bits wide.

Xicor's X2212 is fabricated with reliable n-channel floating gate MOS technology. For systems where RAM nonvolatility or *in-the-circuit* ROM changes by TTL signals are important, the Xicor X2212 is an ideal choice.

### PIN CONFIGURATION 18 PIN DIP .300"



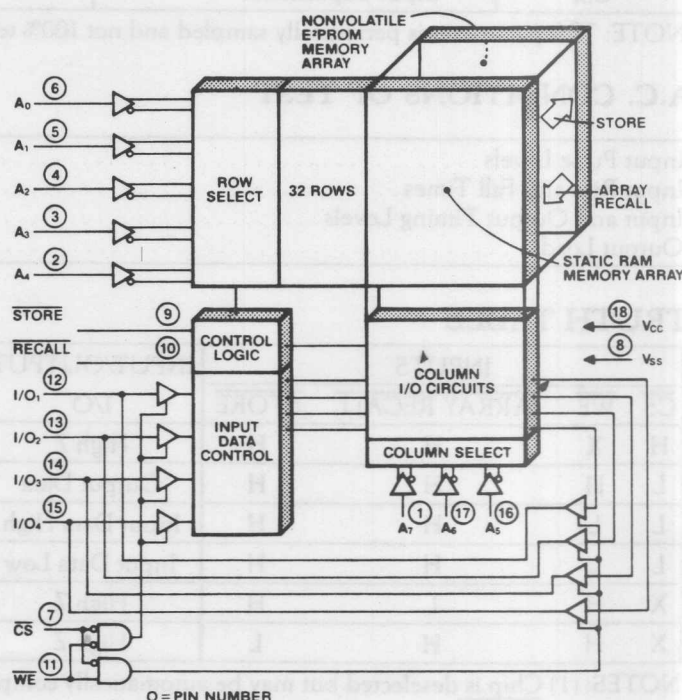
### LOGIC SYMBOL



### PIN NAMES

A <sub>0</sub> –A <sub>7</sub>	ADDRESS INPUTS
I/O <sub>1</sub> –I/O <sub>4</sub>	DATA INPUT/OUTPUT
WE	WRITE ENABLE
CS	CHIP SELECT
ARRAY RECALL	ARRAY RECALL
STORE	STORE
V <sub>CC</sub>	+5V
V <sub>SS</sub>	GROUND
NC	NO CONNECT

### FUNCTIONAL DIAGRAM X2212 (256 x 4)



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Advanced data sheet effective March 1981 Revision B

**ABSOLUTE MAXIMUM RATINGS\***

Temperature Under Bias	-10°C to +85°C
Storage Temperature	-65°C to +125°C
Voltage on Any Pin with Respect to Ground	-1.0V to +6V
D.C. Output Current	5mA

**\*COMMENT**

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and the functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**X2212 D.C. AND OPERATING CHARACTERISTICS**

$T_A = 0^\circ\text{C}$  to  $70^\circ\text{C}$ ,  $V_{CC} = +5\text{V} \pm 5\%$ , unless otherwise specified.

Symbol	Parameter	LIMITS			Units	Test Conditions
		Min	Typ <sup>(3)</sup>	Max		
$I_{CC}$	Power Supply Current		40	55	mA	All Inputs = 5.25V $I_{I/O} = 0\text{mA}$ $T_A = 0^\circ\text{C}$
$I_{LI}$	Input Load Current		.1	10	$\mu\text{A}$	$V_{IN} = \text{GND to } 5.25\text{V}$
$I_{LO}$	Output Leakage Current		.1	10	$\mu\text{A}$	$V_{OUT} = \text{GND to } 5.25\text{V}$
$V_{IL}$	Input Low Voltage	-1.0		.8	V	
$V_{IH}$	Input High Voltage	2.0		$V_{CC}$	V	
$V_{OL}$	Output Low Voltage			.4	V	$I_{OL} = 4.2\text{mA}$
$V_{OH}$	Output High Voltage	2.4			V	$I_{OH} = -2\text{mA}$

**CAPACITANCE**

$T_A = 25^\circ\text{C}$ ,  $f = 1.0\text{ MHz}$ ,  $V_{CC} = 5\text{V}$

Symbol	Test	Max	Unit	Conditions
$C_{I/O}$	Input/Output Capacitance	5	pF	$V_{I/O} = 0\text{V}$
$C_{IN}$	Input Capacitance	5	pF	$V_{IN} = 0\text{V}$

NOTE: This parameter is periodically sampled and not 100% tested.

**A.C. CONDITIONS OF TEST**

Input Pulse Levels	0 Volt to 3.0 Volt
Input Rise and Fall Times	10 nsec
Input and Output Timing Levels	1.5 Volts
Output Load	1 TTL Gate and $C_L = 100\text{ pF}$

**TRUTH TABLE**

INPUTS				INPUT/OUTPUT I/O	MODE
$\overline{CS}$	$\overline{WE}$	ARRAY RECALL	STORE		
H	X	H	H	High Z	Not Selected <sup>(1)</sup>
L	H	H	H	Output Data	Read RAM
L	L	H	H	Input Data High	Write "1" RAM
L	L	H	H	Input Data Low	Write "0" RAM
X	H	L	H	High Z	Array Recall
X	H	H	L	High Z	Nonvolatile Storing <sup>(2)</sup>

NOTES: (1) Chip is deselected but may be automatically completing a store cycle.

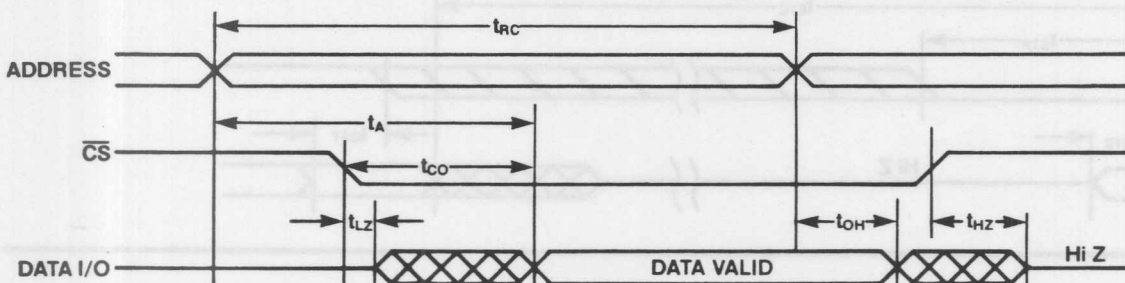
(2)  $\overline{STORE} = L$  is required only to initiate the store cycle, after which the store cycle will be automatically completed ( $\overline{STORE} = X$ ).

**X2212 A.C. CHARACTERISTICS**

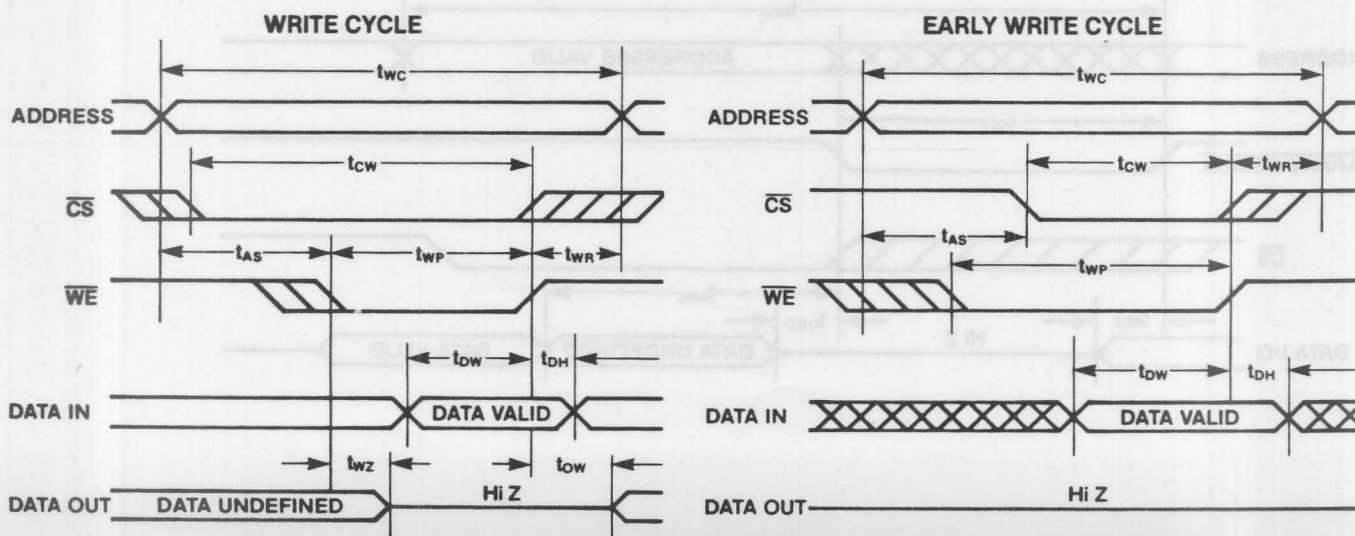
$T_A = 0^\circ\text{C}$  to  $70^\circ\text{C}$ ,  $V_{CC} = +5\text{V} \pm 5\%$ , unless otherwise specified.

**READ CYCLE**

Symbol	Parameter	LIMITS			
		Min	Typ <sup>(3)</sup>	Max	Units
$t_{RC}$	Read Cycle Time	300			ns
$t_A$	Access Time			300	ns
$t_{CO}$	Chip Select to Output Valid			200	ns
$t_{OH}$	Output Hold from Address Change	50			ns
$t_{LZ}$	Chip Select to Output in Low Z	10			ns
$t_{HZ}$	Chip Deselect to Output in High Z	10		100	ns

**WRITE CYCLE**

Symbol	Parameter	LIMITS			
		Min	Typ <sup>(3)</sup>	Max	Units
$t_{WC}$	Write Cycle Time	300			ns
$t_{CW}$	Chip Select to End of Write	150			ns
$t_{AS}$	Address Set-up Time	50			ns
$t_{WP}$	Write Pulse Width	100			ns
$t_{WR}$	Write Recovery Time	25			ns
$t_{DW}$	Data Valid to End of Write	100			ns
$t_{DH}$	Data Hold Time	20			ns
$t_{WZ}$	Write Enable to Output in High Z	10		100	ns
$t_{OW}$	Output Active from End of Write	10			ns

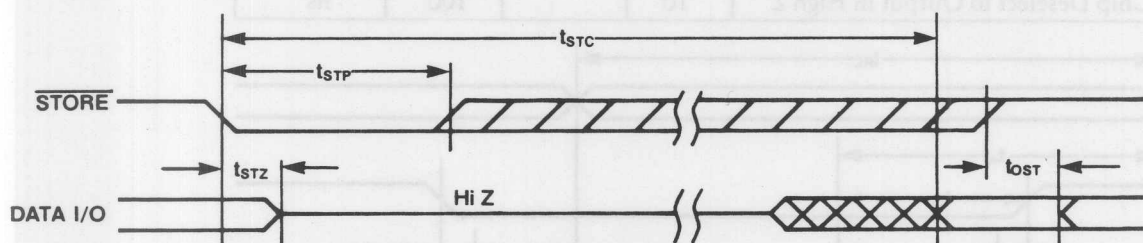




## STORE CYCLE

Symbol	Parameter	LIMITS			Units
		Min	Typ <sup>(3)</sup>	Max	
$t_{STC}$	Store Cycle Time			10	ms
$t_{STP}$	Store Pulse Width	100			ns
$t_{STZ}$	Store to Output in High Z			100	ns
$t_{OST}$	Output Active from End of Store	10			ns

**NUMBER OF STORE CYCLES:** Based on presently available data, the X2212 is expected to perform typically 5,000 valid store cycles. A minimum number of 1,000 valid store cycles is specified.

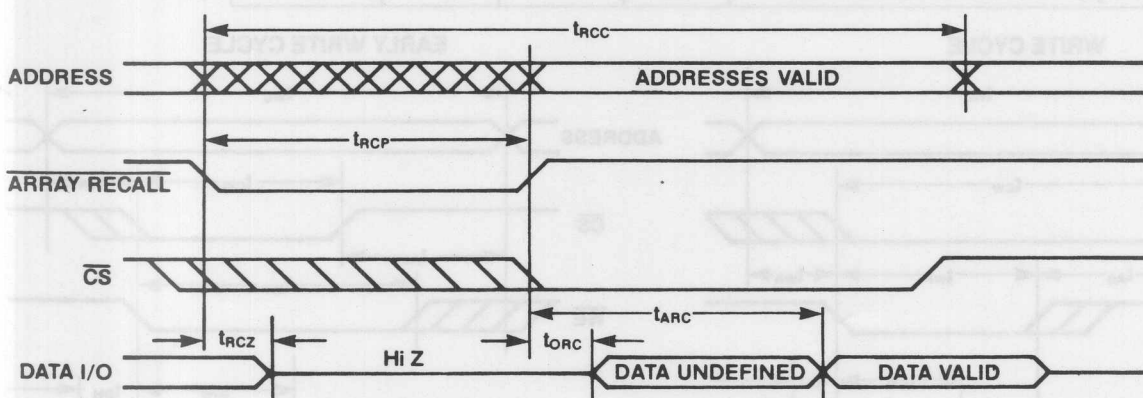


## ARRAY RECALL CYCLE

Symbol	Parameter	LIMITS			Units
		Min	Typ <sup>(3)</sup>	Max	
$t_{RCC}$	Array Recall Cycle Time	1500	1000		ns
$t_{RCP}$	Recall Pulse Width	750			ns
$t_{RCZ}$	Recall to Output in High Z			100	ns
$t_{ORC}$	Output Active from End of Recall	10			ns
$t_{ARC}$	Recalled Data Access Time from End of Recall			600	ns

**NUMBER OF RECALL CYCLES:** After data has been stored properly in the non-volatile memory (E<sup>2</sup>PROM), the X2212 is expected to recall this data an unlimited number of times during the lifetime of the device.

NOTE: (3) Typical values are for  $T_A = 25^\circ\text{C}$  and nominal supply voltages.



**X2212 DEVICE OPERATION****ADDRESSES ( $A_0$ - $A_7$ ):**

The eight address inputs select one of the 256 4-bit words.

**CHIP-SELECT ( $\overline{CS}$ ):**

The chip select terminal affects the data-in/data-out and write enable terminals. When chip-select is high, the I/O terminals are in the floating or high impedance state.

**WRITE ENABLE ( $\overline{WE}$ ):****RAM READ/WRITE CYCLES**

The RAM read or RAM write mode is selected through the write enable terminal when  $\overline{CS}$  is low. A logic high selects the RAM read mode; a logic low selects the RAM write mode.

**STORE ( $\overline{STORE}$ ):****NONVOLATILE E<sup>2</sup>PROM WRITE CYCLE**

Modification of data in the E<sup>2</sup>PROM memory is controlled by the  $\overline{STORE}$  terminal. A low logic  $\overline{STORE}$  signal applied to a device defines a store cycle which transfers a complete 256 x 4-bit copy of all 256 x 4-bit RAM storage locations into the corresponding 1024-bit locations of the overlaid nonvolatile E<sup>2</sup>PROM memory. The data in the E<sup>2</sup>PROM has been modified and is a "snapshot copy" of the current RAM data. The original data in the RAM remains valid. A low logic  $\overline{STORE}$  signal initiates an automatic internal store operation. A low logic  $\overline{STORE}$  into a device also inhibits write enable and array recall: data-in/data-out terminals are in a high impedance state. The inhibited terminals are enabled by either automatic completion of the internal store operation or upon a high logic  $\overline{STORE}$ , whichever is longer. A store cycle can take place when  $\overline{CS}$  is high or low. Data stored in the E<sup>2</sup>PROM remains valid with or without power supplied.

Care must be taken to prevent an unintentional initiation of a store cycle during power-up and power-down. A low logic ARRAY RECALL will inhibit the initiation of a STORE operation. In many microcomputer systems the system reset command can be used during power-up and power-down to generate a low ARRAY RECALL. Another means of assuring a store cycle will not be initiated during power-up or power-down is to keep  $\overline{STORE}$  high, for example by tying the input through a pullup resistor to  $V_{CC}$ , to assure that  $\overline{STORE}$  approximately equals  $V_{CC}$ . In addition, the STORE operation is inhibited for  $V_{CC}$  approximately less than 3 volts.

**ARRAY RECALL (ARRAY RECALL):  
NONVOLATILE E<sup>2</sup>PROM READ CYCLE**

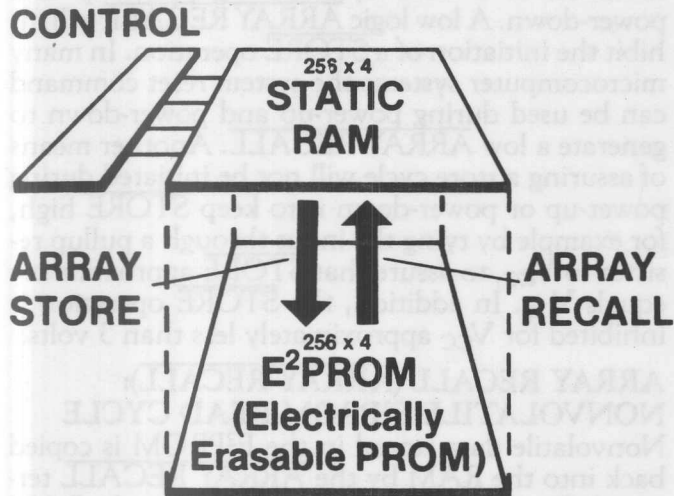
Nonvolatile data stored in the E<sup>2</sup>PROM is copied back into the RAM by the ARRAY RECALL terminal. Once the E<sup>2</sup>PROM data is back in the RAM it can then be accessed by normal RAM read or write cycles. A low logic ARRAY RECALL into a device initiates a cycle that in a single operation transfers the entire 1024-bit E<sup>2</sup>PROM array data bit-for-bit into the 1024-bit RAM memory. The E<sup>2</sup>PROM data overwrites any data then existing in the RAM at the beginning of an ARRAY RECALL cycle. The data in the E<sup>2</sup>PROM remains unaltered.

A low logic ARRAY RECALL inhibits the STORE terminal. An array recall cycle can take place when  $\overline{CS}$  is high or low.

**DATA-IN/DATA-OUT ( $I/O_1$ - $I/O_4$ ):**

Data can be written into the RAM section of a selected device when the write enable input is low. The three-state output buffer provides direct TTL compatibility. The I/O terminals are in the high impedance state when chip select is high or whenever a write operation is being performed.

## MEMORY ORGANIZATION



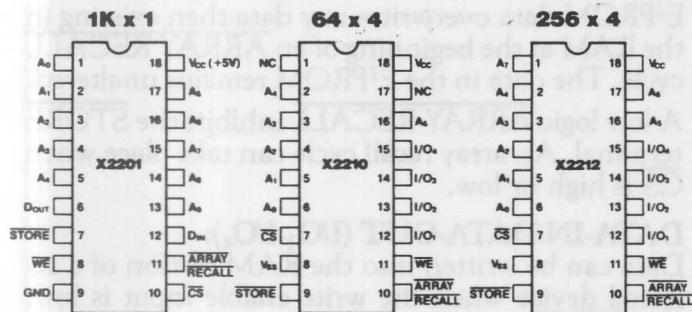
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## A GROWING FAMILY OF NONVOLATILE STATIC RAMS

Available for immediate delivery, the X2201 is the first single 5V supply nonvolatile static RAM and is organized 1K x 1 bits. To meet the further needs of many microcomputer based systems two new nonvolatile RAMs complement the X2201. The X2210 is organized 64 x 4 bits; the X2212 is organized 256 x 4 bits. For maximum system design flexibility, the X2210 and X2212 have compatible pin-outs and can be exchanged in the same 18-pin socket.